

Features

- TrenchFET® Power MOSFET: 1.8-V Rated
- Gate-Source ESD Protected: 2000 V
- High-Side Switching
- Low On-Resistance: 1.2 Ω
- Low Threshold: 0.8 V (typ)
- Fast Switching Speed: 14 ns
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

BENEFITS

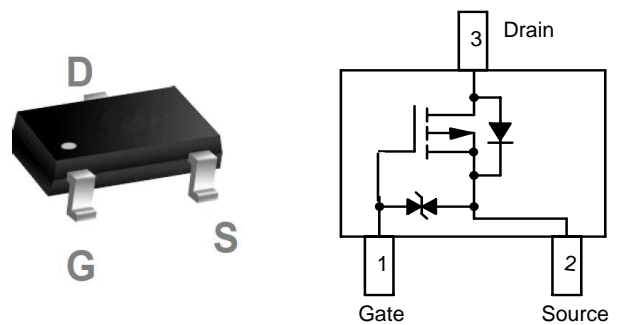
- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

Product Summary

BVDSS	RDSON	ID
-20V	1200mΩ	-0.35A

Applications

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

SOT-523 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 6	V
$I_D@T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-0.35	A
$I_D@T_c=70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-0.4	A
I_{DM}	Pulsed Drain Current ²	-1	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	0.15	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

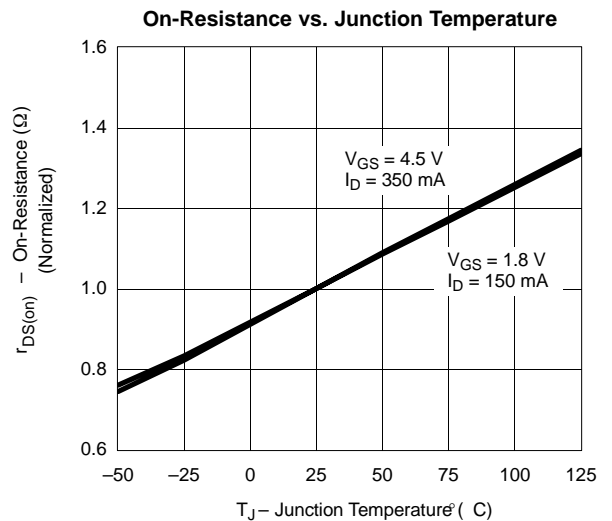
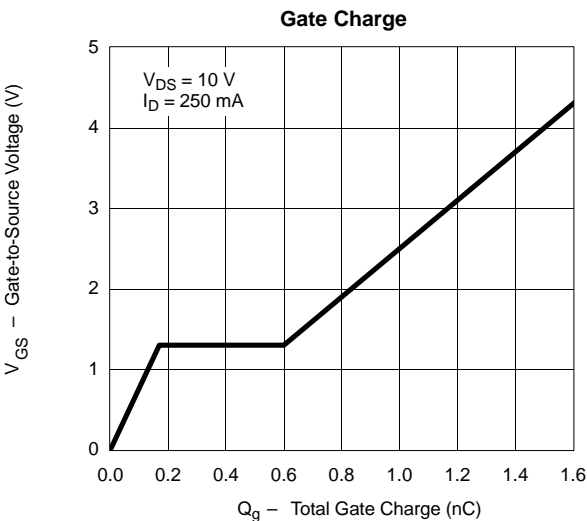
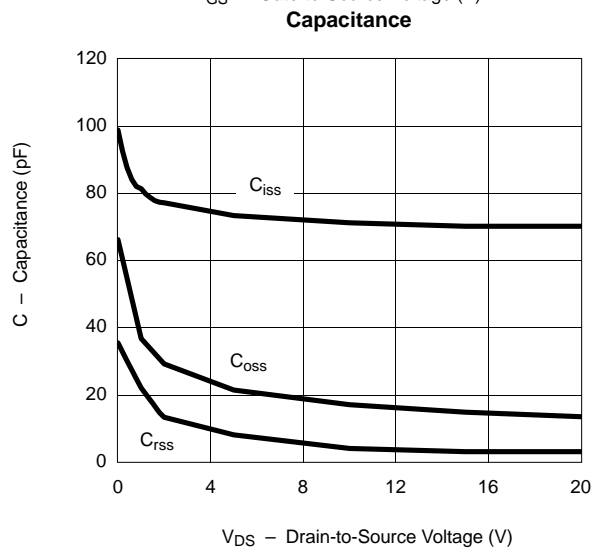
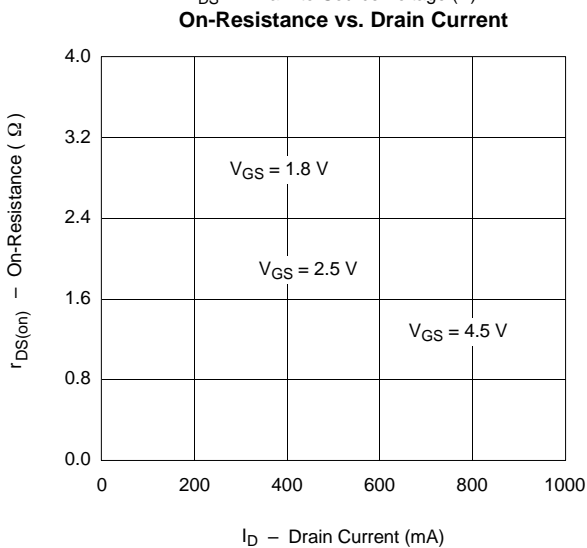
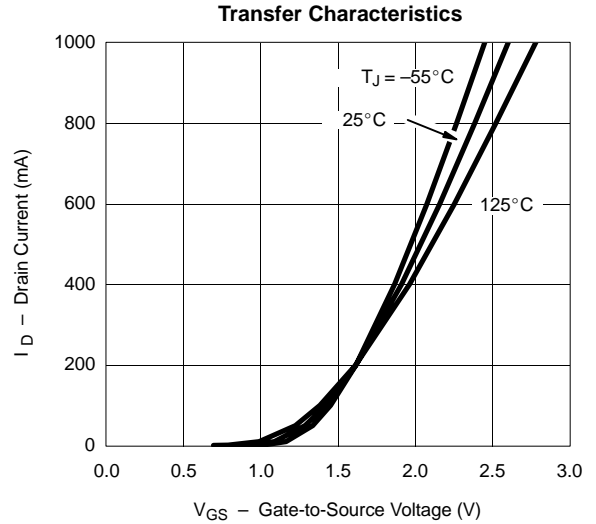
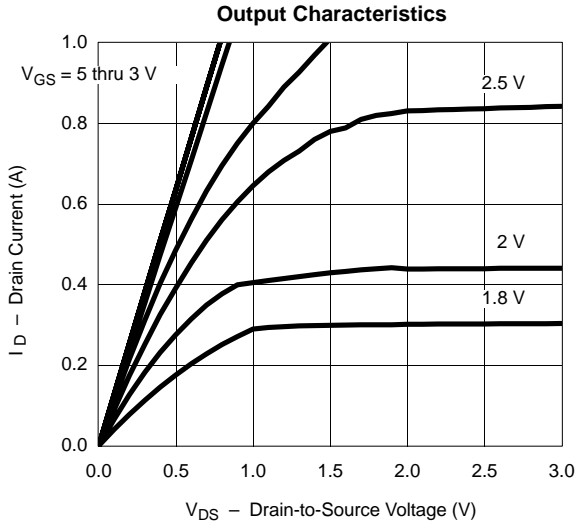
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.016	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-0.35A	---	0.8	1.2	Ω
		V _{GS} =-2.5V, I _D =-0.3A	---	1.2	1.6	
		V _{GS} =-1.8V, I _D =-0.01A	---	1.8	2.7	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.45	---	---	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	3.97	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-16V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±8V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-1A	---	6.2	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	9.5	12	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-1A	---	1500	---	pC
Q _{gs}	Gate-Source Charge		---	150	---	
Q _{gd}	Gate-Drain Charge		---	450	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-15V, V _{GS} =-4.5V, R _G =3.3Ω, I _D =-1A	---	5	---	ns
T _r	Rise Time		---	9	---	
T _{d(off)}	Turn-Off Delay Time		---	35	---	
T _f	Fall Time		---	11	---	

Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

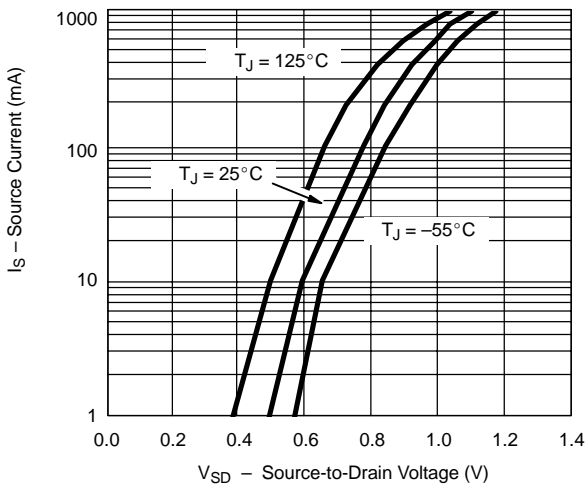
Typical Characteristics

For the following graphs, p-channel negative polarities for all voltage and current values are represented as positive values.

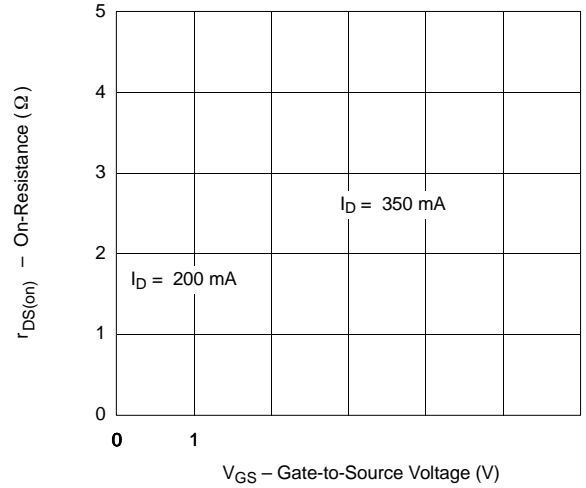


Typical Characteristics

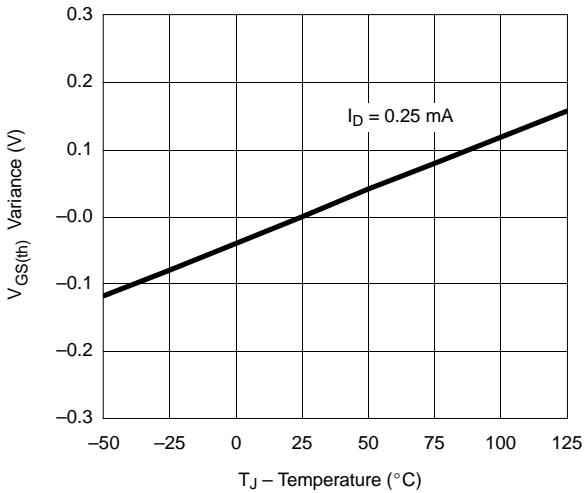
Source-Drain Diode Forward Voltage



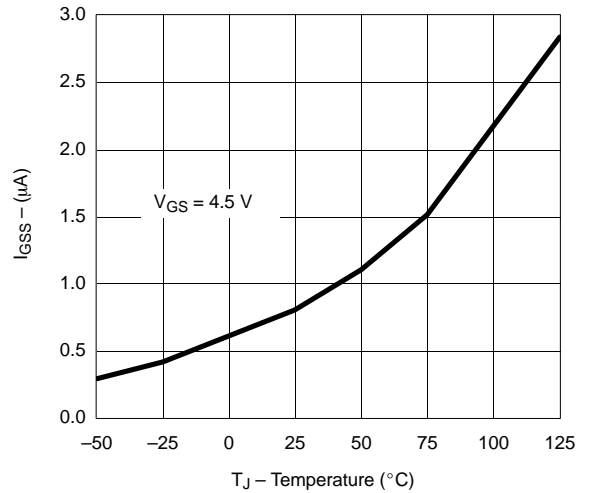
On-Resistance vs. Gate-to-Source Voltage



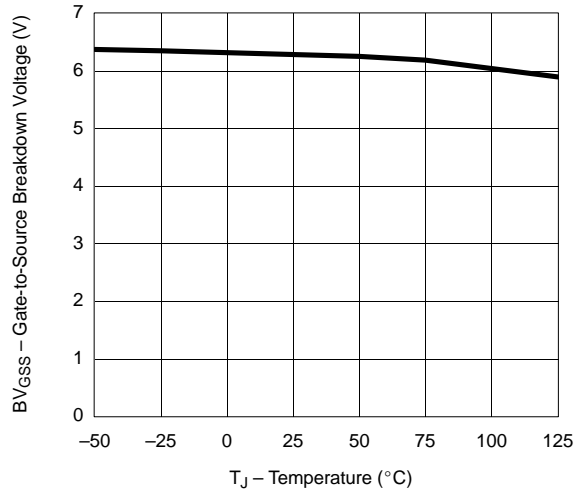
Threshold Voltage Variance vs. Temperature



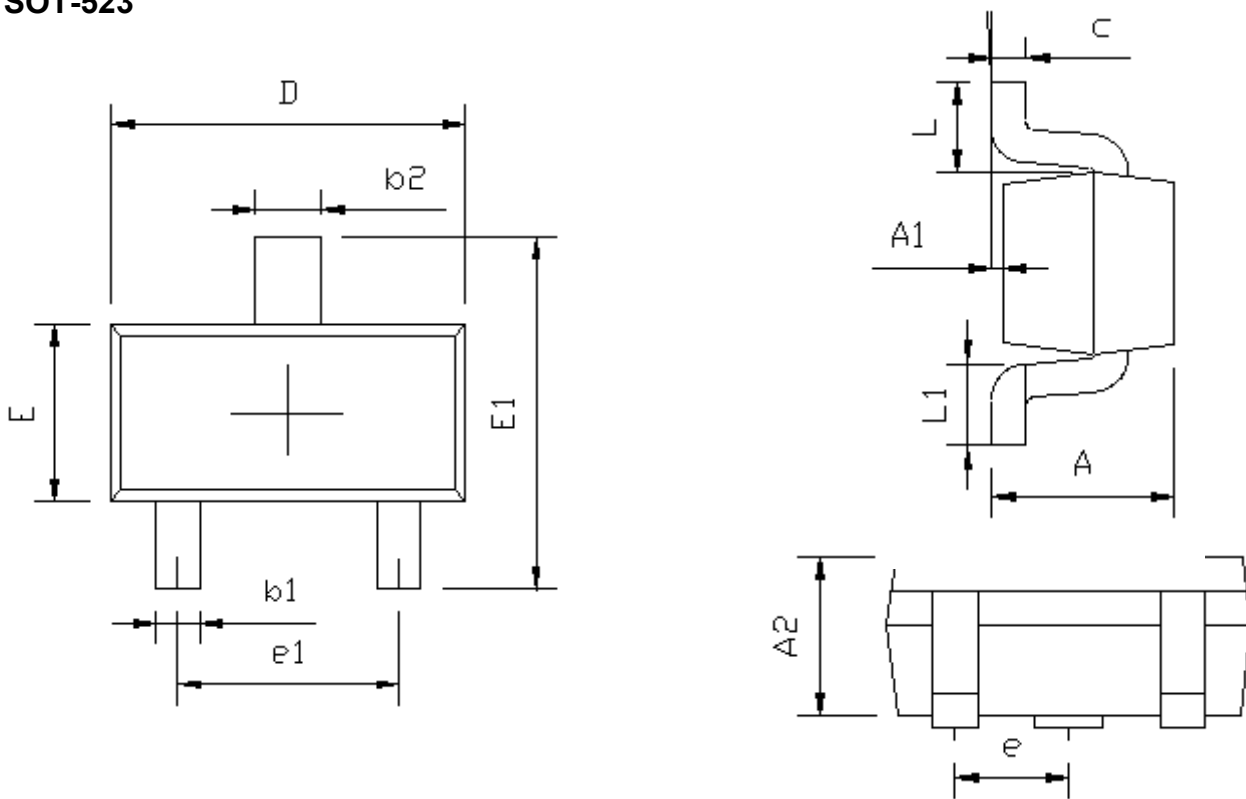
IGSS vs. Temperature



BVGSS vs. Temperature

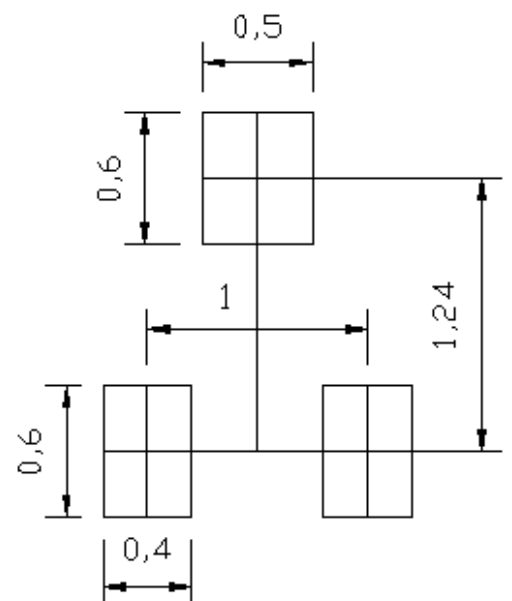


SOT-523



SYMBOLS	SOT-523			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN





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